



KJ300RN02S7

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- Surface-mounted package
- Advanced trench cell design
- Extremely low threshold voltage
- ESD protected

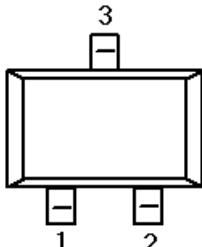
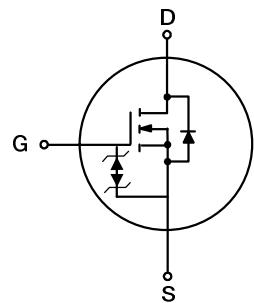
1.2 Applications

- Portable appliances
- High speed switch
- Battery management
- Low power DC to DC Converter

1.3 Quick reference

- $BV \leq 20\text{ V}$
- $P_{tot} \leq 0.27\text{ W}$
- $I_D \leq 0.9\text{ A}$
- $R_{DS(ON)} \leq 0.22\Omega @ V_{GS} = 4.5\text{ V}$
- $R_{DS(ON)} \leq 0.33\Omega @ V_{GS} = 2.5\text{ V}$
- $R_{DS(ON)} \leq 0.48\Omega @ V_{GS} = 1.8\text{ V}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)		
2	Source(S)		
3	Drain(D)	 Top View SOT-723	

**KJ300RN02S7**

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_A = 25^\circ C$	20	-	V
V_{GS}	Gate-Source Voltage	$T_A = 25^\circ C$	-	± 10	V
I_D^*	Drain Current	$T_A = 25^\circ C, V_{GS} = 4.5 V$	-	0.9	A
		$T_C = 100^\circ C, V_{GS} = 4.5 V$	-	0.57	
$I_{DM}^{**,**}$	Pulsed Drain Current	$T_A = 25^\circ C, V_{GS} = 4.5 V$	-	3.6	A
P_{tot}	Total Power Dissipation	$T_A = 25^\circ C$	-	0.27	W
T_{stg}	Storage Temperature		- 55	150	$^\circ C$
T_J	Junction Temperature		-	150	$^\circ C$
I_S	Diode Forward Current	$T_A = 25^\circ C$	-	0.9	A
$R_{\theta JA}$	Thermal Resistance- Junction to Ambient		-	461	$^\circ C / W$

Notes :

- * Pulse width $\leq 300 \mu s$, duty cycle $\leq 2 \%$
- ** Surface Mounted on minimum footprint pad area.
- *** Limited by bonding wire

4. Marking Information

Product Name	Marking
KJ300RN02S7	32

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ300RN02S7	SOT723			8000	

Note: KUAIJIEXIN defines " Green " as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)



KJ300RN02S7

6. Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

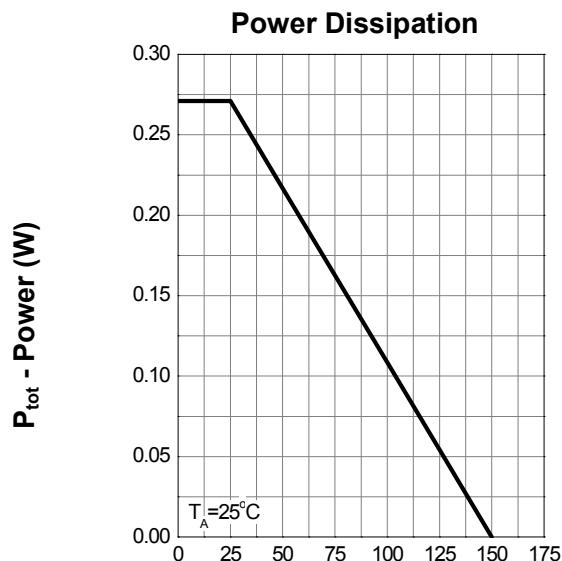
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{DS} = 250 \mu\text{A}$	20	-	-	V
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu\text{A}$	0.5	-	1	V
I_{DSS}	Drain Leakage Current	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$ $T_J = 85^\circ\text{C}$	-	-	1	μA
I_{GSS}	Gate Leakage Current	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	± 10	uA
$R_{DS(\text{ON})}^a$	On-State Resistance	$V_{GS} = 4.5 \text{ V}, I_{DS} = 0.5 \text{ A}$	-	0.19	0.22	Ω
		$V_{GS} = 2.5 \text{ V}, I_{DS} = 0.4 \text{ A}$	-	0.27	0.33	
		$V_{GS} = 1.8 \text{ V}, I_{DS} = 0.3 \text{ A}$	-	0.37	0.48	
Diode Characteristics						
V_{SD}^a	Diode Forward Voltage	$I_{SD} = 0.5 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1.2	V
Dynamic Characteristics ^b						
C_{iss}	Input Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 10 \text{ V}$ Frequency = 1 MHz	-	101	-	pF
C_{oss}	Output Capacitance		-	47	-	
C_{rss}	Reverse Transfer Capacitance		-	39	-	
$t_d(\text{on})$	Turn-on Delay Time	$V_{DS} = 10 \text{ V}, V_{GEN} = 4.5 \text{ V},$ $R_G = 3.9 \Omega, R_L = 20 \Omega,$ $I_{DS} = 0.5 \text{ A}$	-	68	-	nS
t_r	Turn-on Rise Time		-	53	-	
$t_d(\text{off})$	Turn-off Delay Time		-	105	-	
t_f	Turn-off Fall Time		-	20	-	
Gate Charge Characteristics ^b						
Q_g	Total Gate Charge	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{DS} = 0.5 \text{ A}$	-	1.02	-	nC
Q_{gs}	Gate-Source Charge		-	0.12	-	
Q_{gd}	Gate-Drain Charge		-	0.15	-	

Notes :

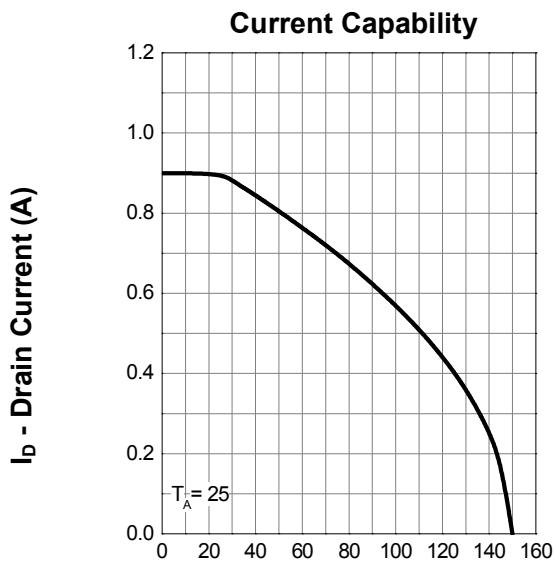
a : Pulse test ; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

b : Guaranteed by design, not subject to production testing

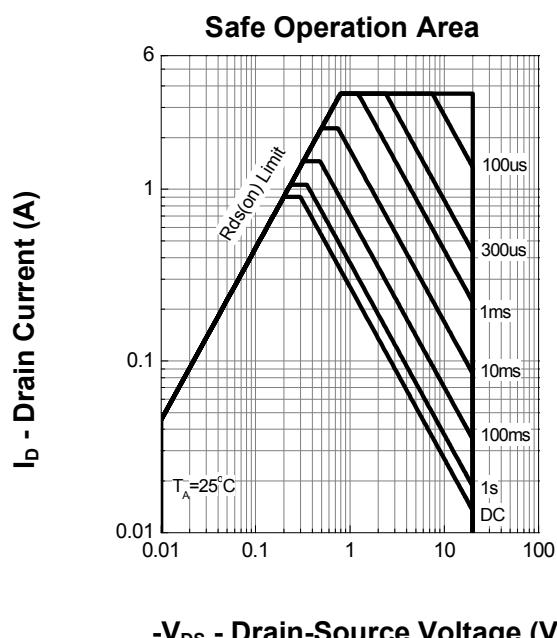
7. Typical Characteristics



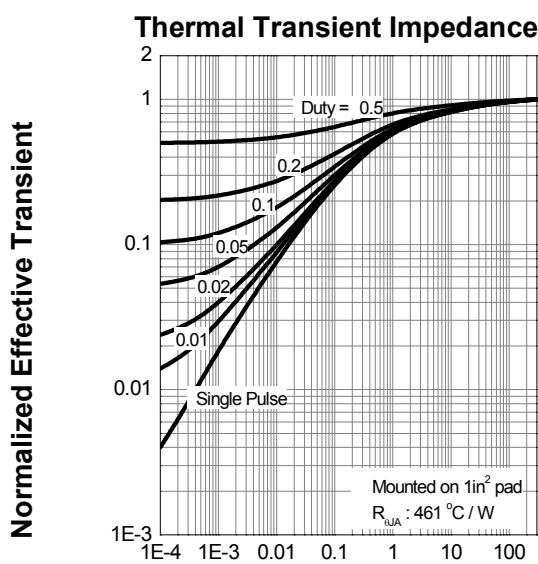
T_j - Junction Temperature (°C)



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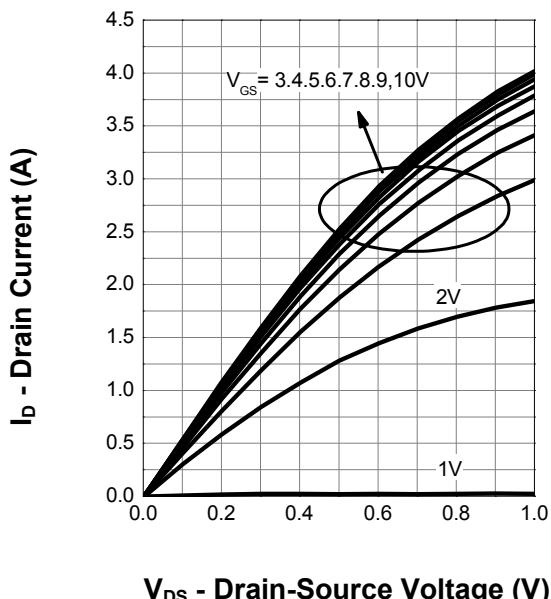
-V_{DS} - Drain-Source Voltage (V)



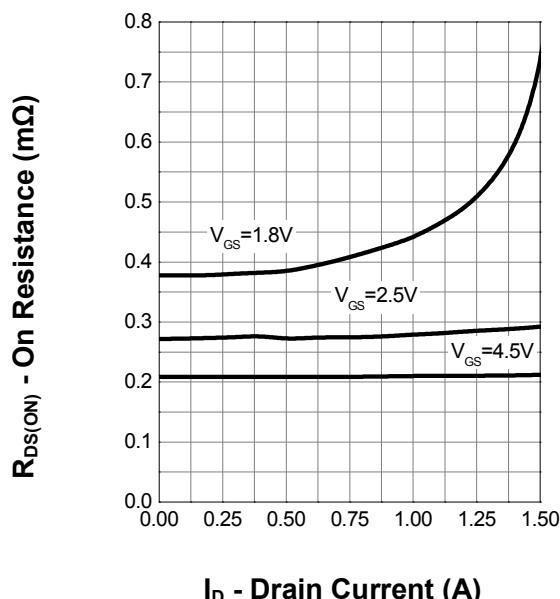
Square Wave Pulse Duration (sec)

7. Typical Characteristics (cont.)

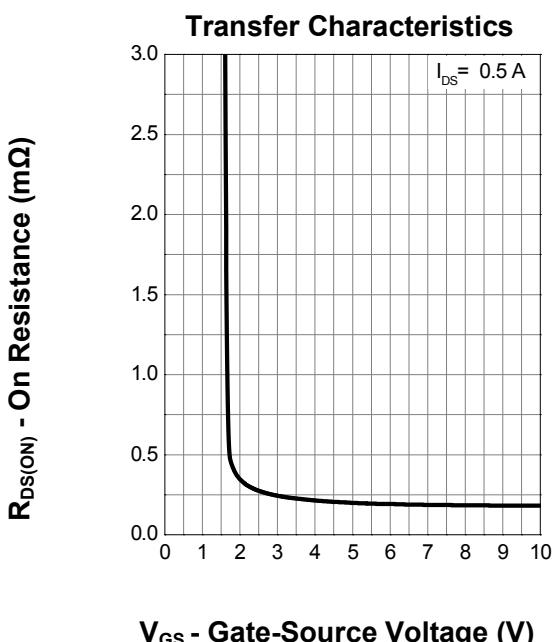
Output Characteristics



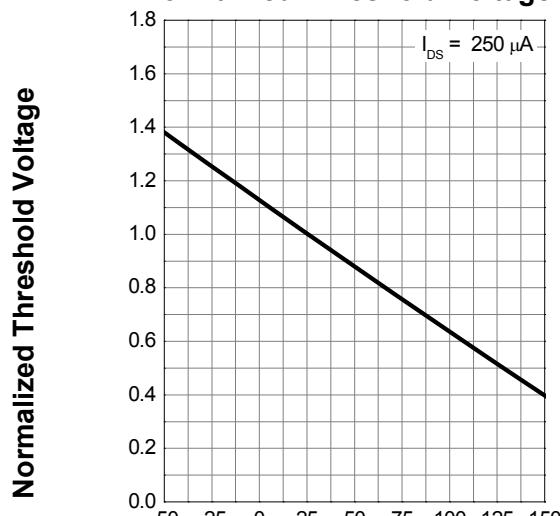
Drain-Source On Resistance



Transfer Characteristics

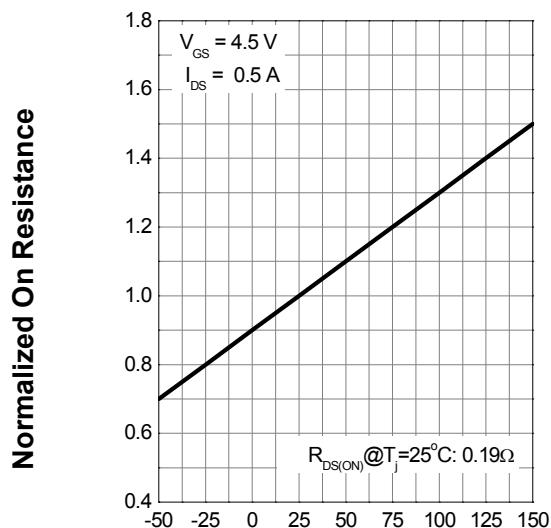


Normalized Threshold Voltage

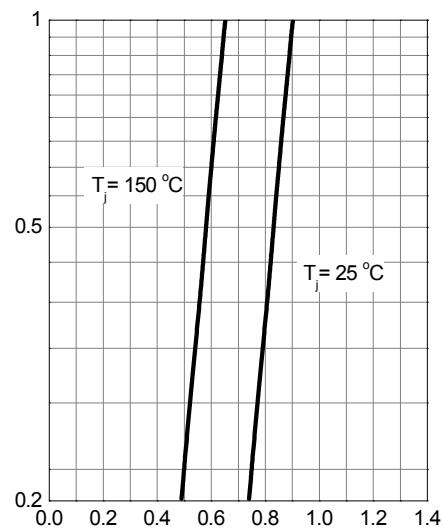


7. Typical Characteristics (cont.)

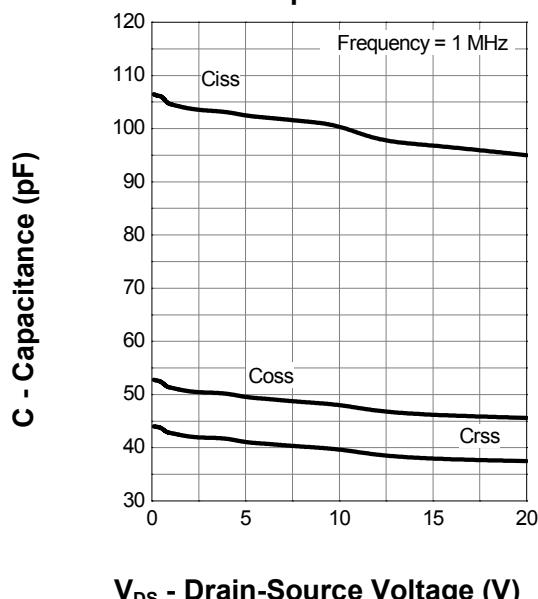
Normalized On Resistance



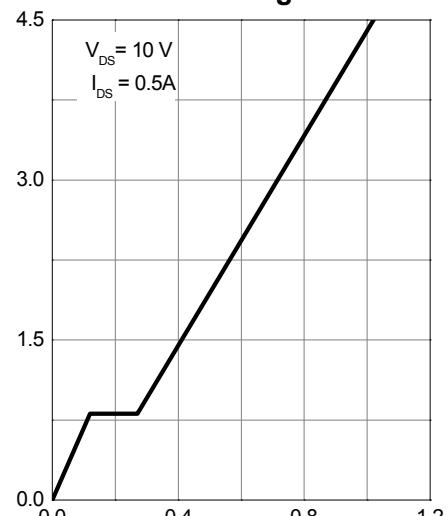
Current Diode Forward



Capacitance

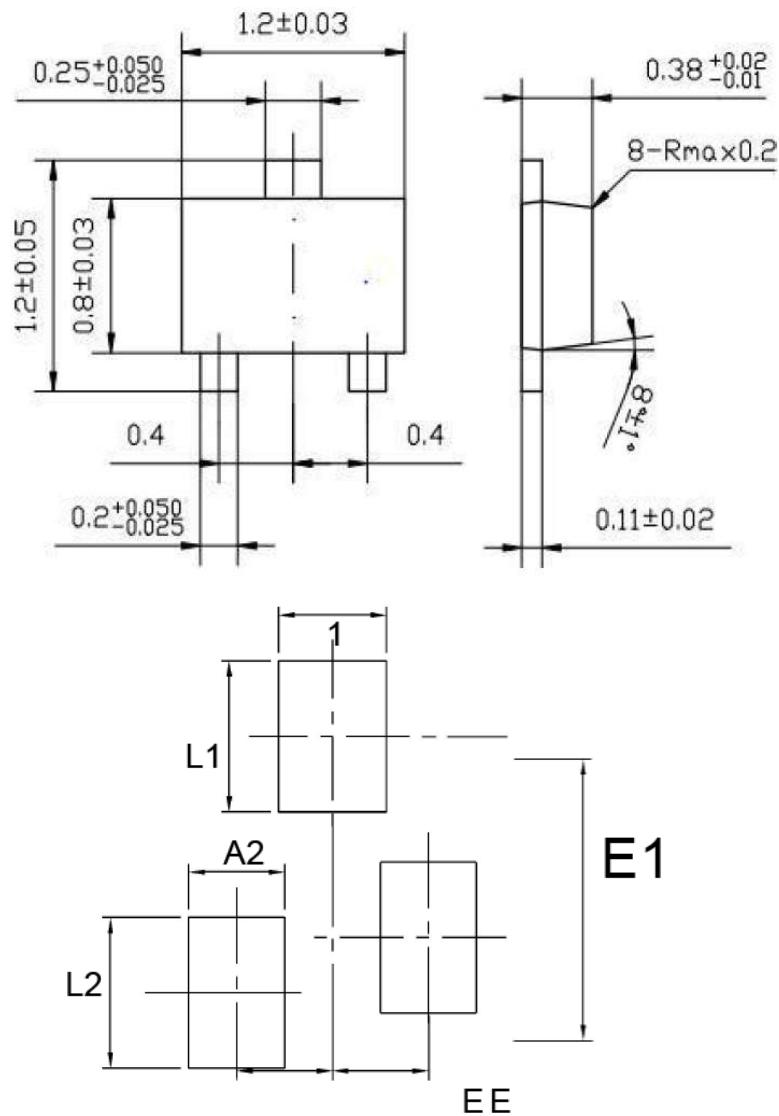


Gate Charge



8. Package Dimensions

SOT-723 Package



Symbol	A1	A2	L1	L2	E1	E
Dimensions	0.45mm	0.40mm	0.63mm	0.63mm	1.17mm	0.40mm